



AMERICAN MICROSEMICONDUCTOR

GERMANIUM DOIDES

TYPE NO.	PIV (V)	MINIMUM FORWARD CURRENT		I0 RATED MAX(W)	MAX TEMP °C	DESCRIPTION	
		IF(A)	VF(v)			MAT	DRAWING NO.
1N270	100	200m	1.0		90	Ge	Do7
1N34A	60	5.0m	1.0	50m	90	Ge	Do7
1N107	10	150m	1.0	100m	90	Ge	Do7
AA112	15	20m	1.3	24m	100	Ge	Do7
1N64	25	3.0m	1.0	50m	90	Ge	Do7
AA119	45	10m	2.2	35m	75	Ge	Do7
AA113	60	3.5m	1.0	2.5m	100	Ge	Do7
1N73	70	15m	1.5		90	Ge	Do7
AA118	115	30m	2.6			Ge	Do7
AA117	115	30m	3.3			Ge	Do7
1N55	150	5.0m	1.0		90	Ge	Do7
1N771	80	100m	1.0	50m	100s	Ge	Do7
1N772	70	100m	1.0	50m	100s	Ge	Do7
1N773	65	100m	1.0	50m	100s	Ge	Do7
1N307	125	100m	1.0	50m	70	Ge	Do7
1N435	40			60m	75	Ge	Do7
DR366	86	50m	1.0			Ge	Do7
1N733A	65	200m	1.0	65m	100s	Ge	Do7
1N744A	65	200m	1.0	65m	100s	Ge	Do7
1N279	32	100m	1.0	70m	90A	Ge	Do7
1N292	70	100m	1.0	70m	90A	Ge	Do7
1N502	115	100m	0.8	70m	90	Ge	Do7
1N3466	40	200m	1.0	75m	90	Ge	Do7
1N3465	60	200m	1.0	75	90	Ge	Do7
1N281	75	100m	1.0	75m	90	Ge	Do7
1N497	25	100m	1.0	80m	85	Ge	Do7
1N273	32	100m	1.0	80m	90A	Ge	Do7
1N498	46	100m	1.0	80m	85	Ge	Do7
1N289	70	30m	2.0	50m	100	Ge	Do7
1N453	115	100m	1.0			Ge	Do7
1N3865	80	100m	1.0			Ge	Do7
HG5007	40	100m	0.8	80m	90	Ge	Do7
DR314	80	100m	1.0	80m		Ge	Do7
DR330	80	300m	1.0			Ge	Do7
DR303	86	400m	1.0	100m		Ge	Do7
DR302	115	400m	1.0	100m		Ge	Do7
DR379	150	200m	1.0	100m		Ge	Do7
DR272	175	400m	1.0	100m		Ge	Do7
DR321	86	400m	1.0	100m		Ge	Do7
DR213	86	100m	1.0	100m		Ge	Do7
DR326	86	100m	1.0	100m		Ge	Do7
DR313	115	100m	1.0	80m		Ge	Do7
DR324	115	100m	1.0	80m		Ge	Do7
DR463	80	300m	1.0	100m		Ge	Do7
DR303	86	400m	1.0	100m		Ge	Do7

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		IF(A)	VF(v)			MAT	DRAWING NO.
DR329	86	200m	1.0	100m		Ge	Do7
DR306	86	300m	1.0	100m		Ge	Do7
DR308	115	200m	1.0	100m		Ge	Do7
DR309	115	200m	1.0	100m		Ge	Do7
DR328	115	300m	1.0	100m		Ge	Do7
DR328	115	400m	1.0	100m		Ge	Do7
T17G							
1W634							
1N277	125	100m	1.0	100m	90	Ge	Do7
DR327	150	300m	1.0	100m		Ge	Do7
DR305	150	200m	1.0	100m		Ge	Do7
DR272	175	400m	1.0	100m		Ge	Do7
DR312	150	100m	1.0	80m		Ge	Do7
DR325	150	100m	1.0	80m		Ge	Do7
Dr310	175	100m	1.0	80m		Ge	Do7
1N498	46	100m	1.0	80m	85	Ge	Do7
1N499	62	100m	1.0	80m		Ge	Do7
1N501	92	100m	1.0	80m	85	Ge	Do7
1N502	115	100m	0.8	80m	90	Ge	Do7
HG50089	40	100m	0.8	70m	90	Ge	Do7
1W569							
T7G							
EGG109							
T19G							

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